

<b>SANYO</b>	No.2679A	<b>2SC4291</b>
	NPN Triple Diffused Planar Silicon Transistor Ultrahigh-Definition Color Display Horizontal Deflection Output Applications	

**Features**

- High speed ( $t_f = 0.3 \mu s$  max).
- High breakdown voltage ( $V_{CBO} = 1500V$ ).
- High reliability (Adoption of HVP process).
- Adoption of MBIT process.
- On-chip damper diode.

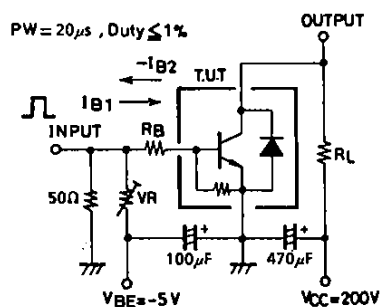
**Absolute Maximum Ratings at  $T_a = 25^\circ C$**

			unit
Collector-to-Base Voltage	$V_{CBO}$	1500	V
Collector-to-Emitter Voltage	$V_{CEO}$	800	V
Emitter-to-Base Voltage	$V_{EBO}$	7	V
Collector Current	$I_C$	5	A
Collector Current (Pulse)	$I_{CP}$	16	A
Collector Dissipation	$P_C$	2.5	W
		$T_c = 25^\circ C$	
Junction Temperature	$T_j$	100	W
Storage Temperature	$T_{stg}$	150	$^\circ C$
		-55 to +150	$^\circ C$

**Electrical Characteristics at  $T_a = 25^\circ C$**

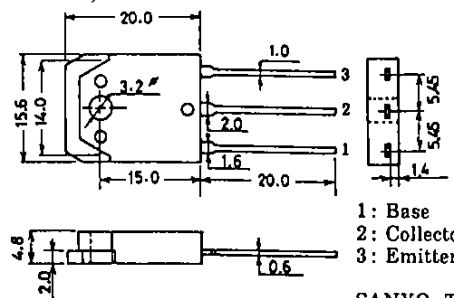
			min	typ	max	unit
Collector Cutoff Current	$I_{CES}$	$V_{CE} = 1500V$			1.0	mA
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 800V, I_E = 0$			10	$\mu A$
Collector Sustain Voltage	$V_{CEO(sus)}$	$I_C = 100mA, I_B = 0$	800			V
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 4V, I_C = 0$	40		130	mA
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 4A, I_B = 1A$			5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 4A, I_B = 1A$			1.5	V
DC Current Gain	$h_{FE(1)}$	$V_{CE} = 5V, I_C = 1A$	8			
	$h_{FE(2)}$	$V_{CE} = 5V, I_C = 4A$	4		6	
Diode Forward Voltage	$V_F$	$I_{EC} = 5A, I_B = 0$			2.0	V
Storage Time	$t_{stg}$	$I_C = 4A, I_{B1} = 0.8A, I_{B2} = -1.6A$			3.0	$\mu s$
Fall Time	$t_f$	$I_C = 4A, I_{B1} = 0.8A, I_{B2} = -1.6A$			0.3	$\mu s$

**Switching Time Test Circuit**



**Package Dimensions 2022A**

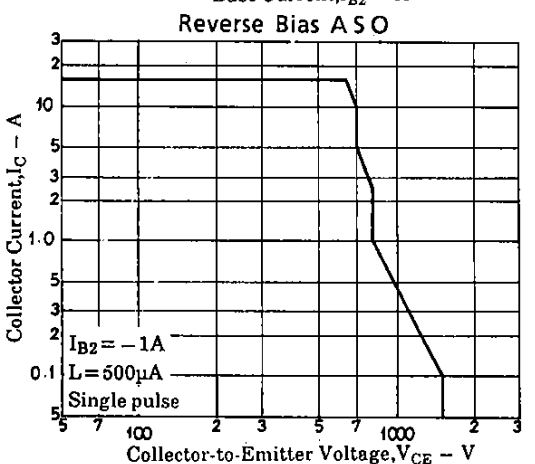
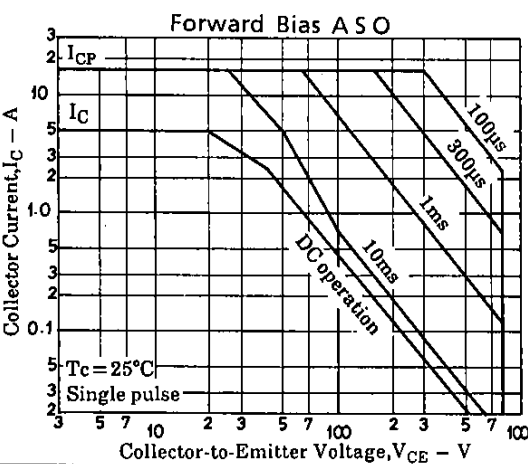
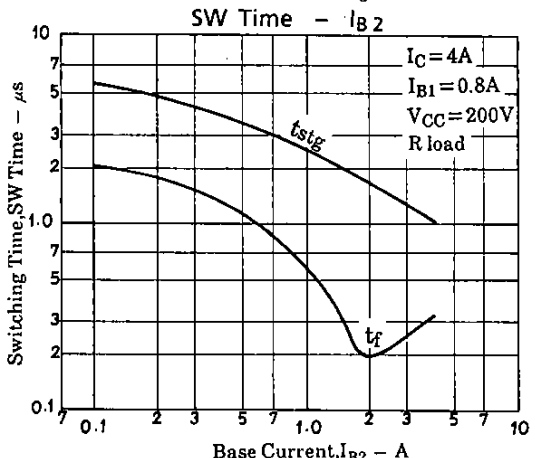
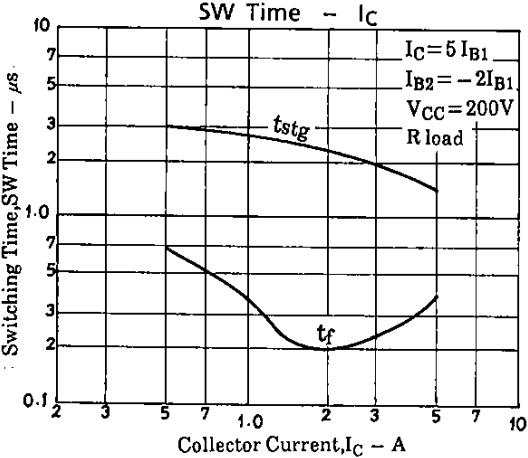
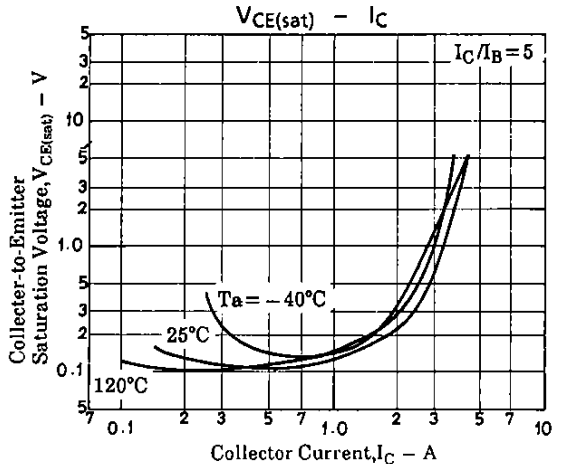
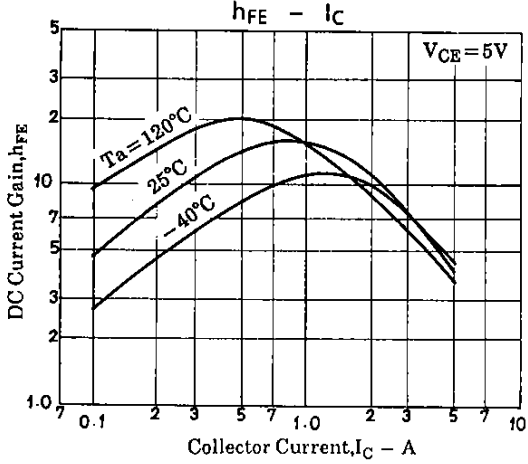
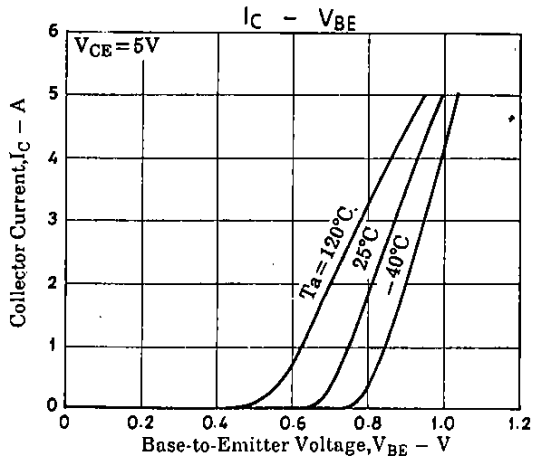
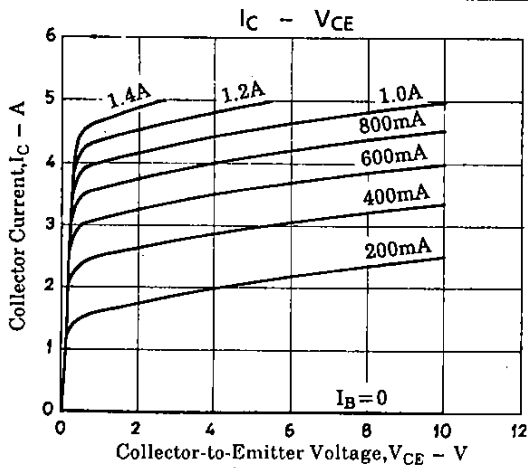
(unit: mm)

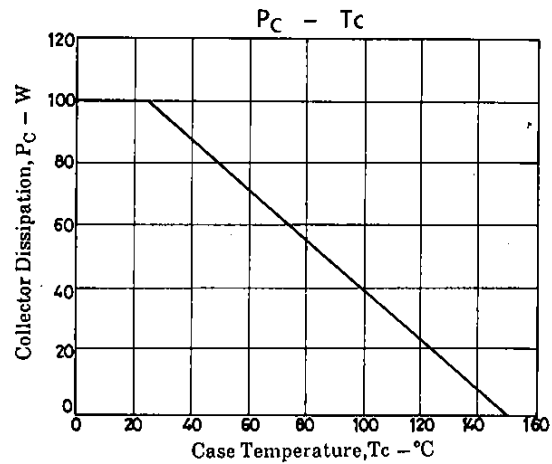
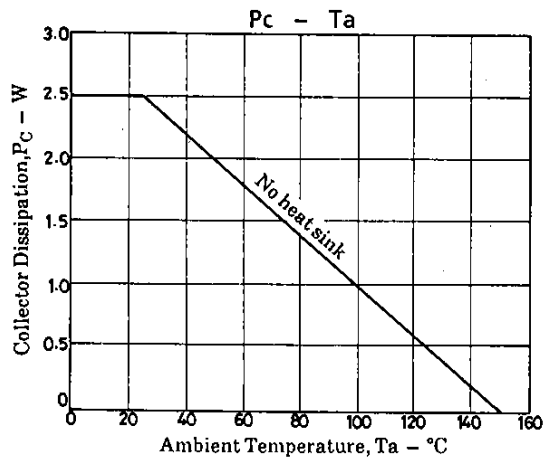


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